Zhiting Lin

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/3512792/publications.pdf

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12	382	1163117 8	1199594 12
papers	citations	h-index	g-index

12	12	12	572
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	GaN-based light-emitting diodes on various substrates: a critical review. Reports on Progress in Physics, 2016, 79, 056501.	20.1	236
2	Performance improvement of GaN-based light-emitting diodes grown on Si(111) substrates by controlling the reactor pressure for the GaN nucleation layer growth. Journal of Materials Chemistry C, 2015, 3, 1484-1490.	5.5	31
3	Growth evolution of AlN films on silicon (111) substrates by pulsed laser deposition. Journal of Applied Physics, 2015, 117, .	2.5	21
4	Achieving High-Performance Blue GaN-Based Light-Emitting Diodes by Energy Band Modification on Al_{<italic>x</italic>}In_{<italic>y</italic>}Ga<sub>1â€“<italic>x</italic>â€“<italic Electron Blocking Layer. IEEE Transactions on Electron Devices, 2017, 64, 472-480.		
5	Effect of residual stress on the microstructure of GaN epitaxial films grown by pulsed laser deposition. Applied Surface Science, 2016, 369, 414-421.	6.1	16
6	Nitridation effect of the Î±-Al₂O₃ substrates on the quality of the GaN films grown by pulsed laser deposition. RSC Advances, 2014, 4, 39651-39656.	3.6	14
7	Effect of InGaAs interlayer on the properties of GaAs grown on Si (111) substrate by molecular beam epitaxy. Journal of Applied Physics, 2014, 116, 193508.	2.5	12
8	Epitaxial growth of high-quality AlN films on metallic nickel substrates by pulsed laser deposition. RSC Advances, 2014, 4, 27399-27403.	3.6	11
9	Growth mechanisms of GaN epitaxial films grown on ex situ low-temperature AlN templates on Si substrates by the combination methods of PLD and MOCVD. Journal of Alloys and Compounds, 2017, 718, 28-35.	5.5	8
10	Employing Al buffer layer with Al droplets-distributed surface to obtain high-quality and stress-free GaN epitaxial films on Si substrates. Journal of Materials Science, 2017, 52, 1318-1329.	3.7	6
11	High-Performance GaN-Based LEDs on Si Substrates: The Utility of <italic>Ex Situ</italic> Low-Temperature AlN Template With Optimal Thickness. IEEE Transactions on Electron Devices, 2017, 64, 4540-4546.	3.0	6
12	Stress management on underlying GaN-based epitaxial films: A new vision for achieving high-performance LEDs on Si substrates. Journal of Applied Physics, 2017, 122, 204503.	2.5	4